

TOSHIBA IGBT MODULE SILICON N CHANNEL IGBT

MG600Q2YS60A

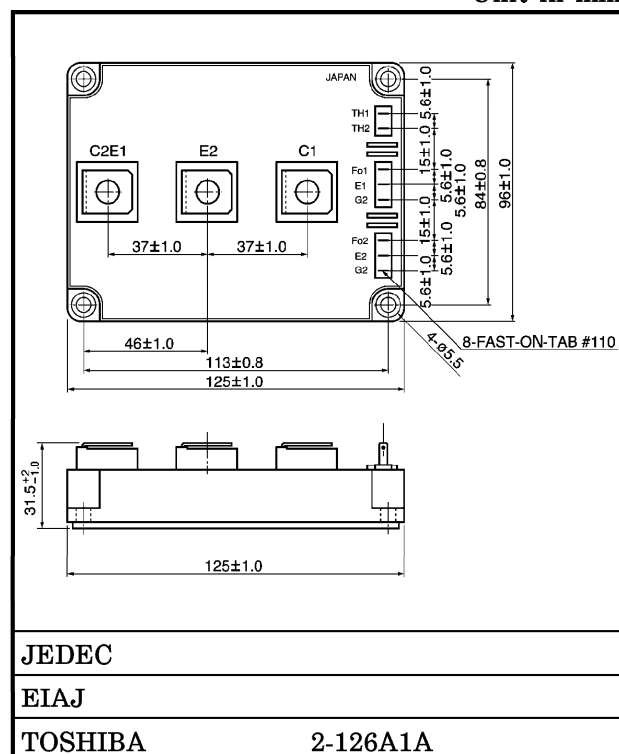
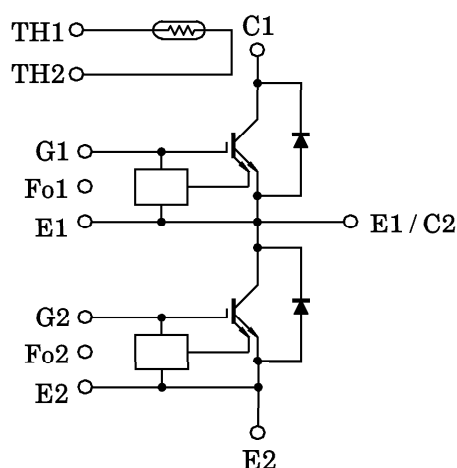
HIGH POWER SWITCHING APPLICATIONS

MOTOR CONTROL APPLICATIONS

Unit in mm

- The Electrodes are Isolated from Case.
- Enhancement-Mode
- Thermal Output Terminal (TH)

EQUIVALENT CIRCUIT



Weight : 680 g

000707EAA1

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MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Emitter Voltage		V _{CES}	1200	V
Gate-Emitter Voltage		V _{GES}	±20	V
Collector Current	DC	I _C	600	A
Forward Current	DC	I _F	600	A
Collector Power Dissipation (T _c = 25°C)		P _C	4300	W
Junction Temperature		T _j	150	°C
Storage Temperature Range		T _{stg}	−40~125	°C
Isolation Voltage		V _{Isol}	2500 (AC 1 min)	V
Screw Torque	Terminal : M8	—	10	N·m
	Mounting : M5	—	3	N·m

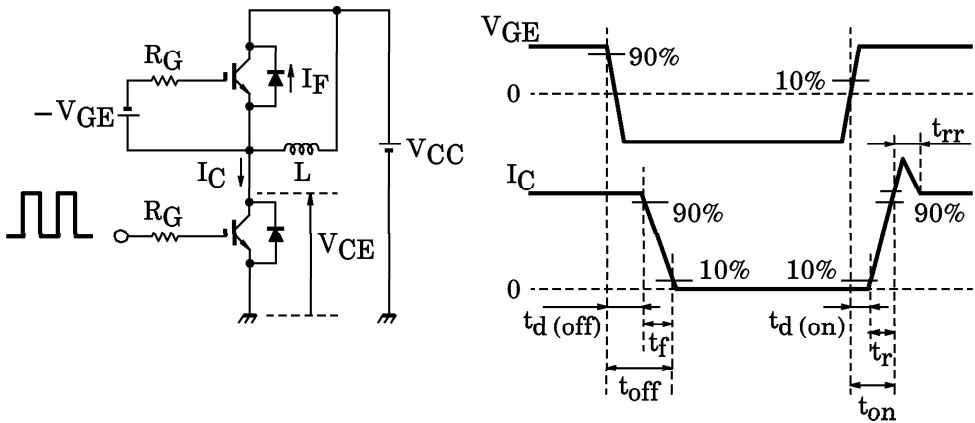
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

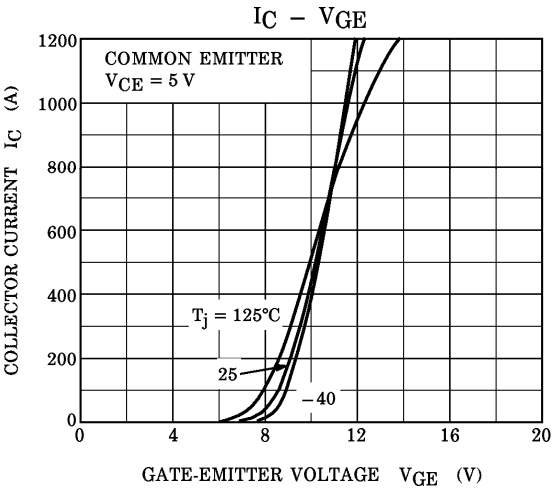
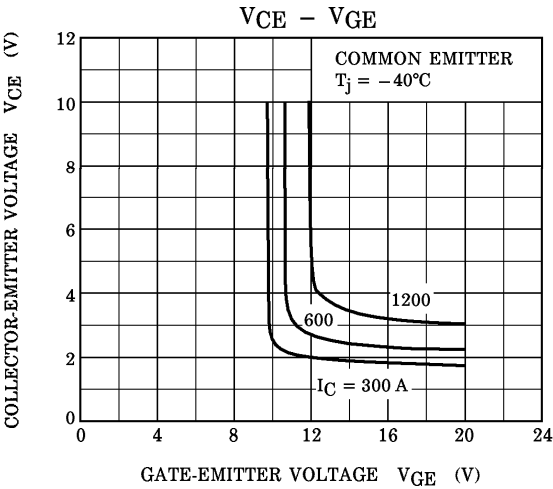
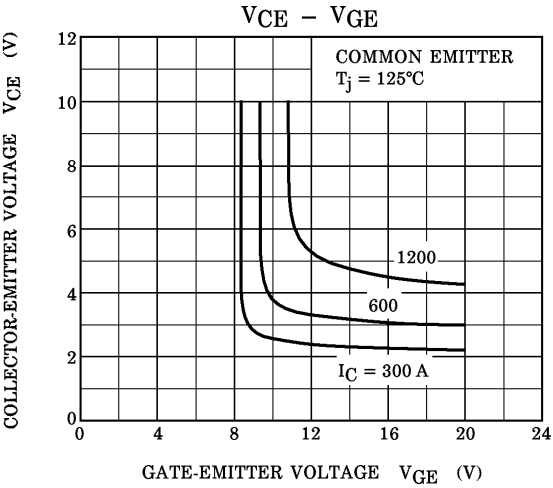
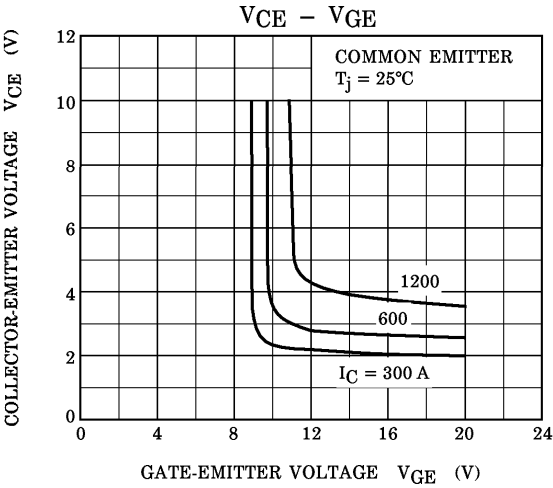
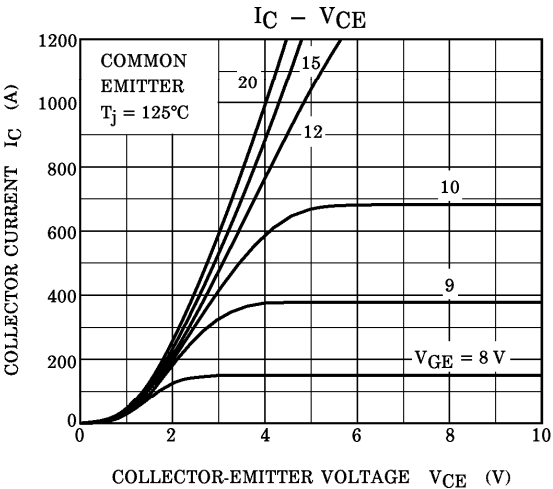
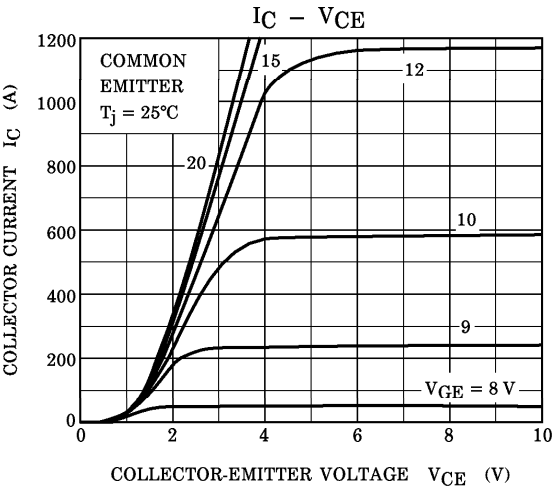
CHARACTERISTIC		SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I _{GES}	V _{GE} = ±20 V, V _{CE} = 0 V		—	—	±10	μA
Collector Cut-Off Current		I _{CES}	V _{CE} = 1200 V, V _{GE} = 0		—	—	1	mA
Gate-Emitter Cut-Off Voltage		V _{GE} (off)	I _C = 600 mA, V _{CE} = 5 V		—	6.7	—	V
Collector-Emitter Saturation Voltage		V _{CE} (sat)	I _C = 600 A,	T _J = 25°C	—	2.7	3.1	V
			V _{GE} = 15 V	T _J = 125°C	—	3.2	3.5	
Input Capacitance		C _{ies}	V _{CE} = 10 V, V _{GE} = 0 V, f = 1 MHz		—	41000	—	pF
Gate-Emitter Voltage		V _{GE}	—		13	15	17	V
Gate Resistance		R _G	—		7.5	—	15	Ω
Switching Time	Turn-On Delay Time	t _d (on)	Inductive Load V _{CC} = 600 V I _C = 600 A V _{GE} = ±15 V R _G = 7.5 Ω (Note)		—	0.3	—	μs
	Rise Time	t _r			—	0.2	—	
	Turn-On Time	t _{on}			—	0.5	—	
	Turn-Off Delay Time	t _d (off)			—	1.3	—	
	Fall Time	t _f			—	0.1	0.3	
	Turn-Off Time	t _{off}			—	1.4	—	
Forward Voltage		V _F	I _F = 600 A,	T _J = 25°C	—	2.2	3.2	V
			V _{GE} = 0 V	T _J = 125°C	—	2.0	—	
Reverse Recovery Time		t _{rr}	I _F = 600 A, V _{GE} = −15 V di / dt = 2000 A / μs		—	0.3	0.5	μs
Thermal Resistance		R _{th} (j-c)	Transistor Stage		—	—	0.029	°C / W
			Diode Stage		—	—	0.056	
RTC Operating Current		I _{Rtc}	T _J = 25°C		1200	—	—	A

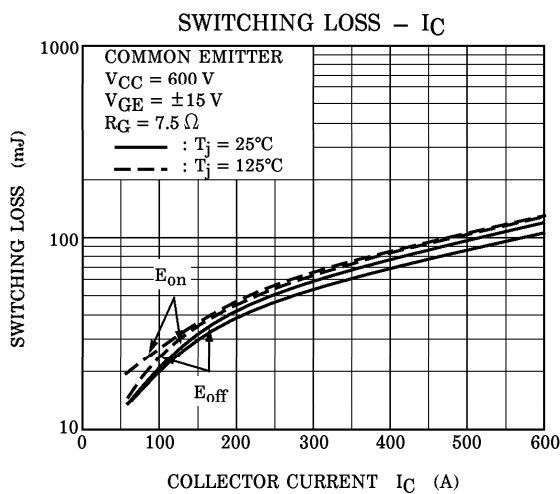
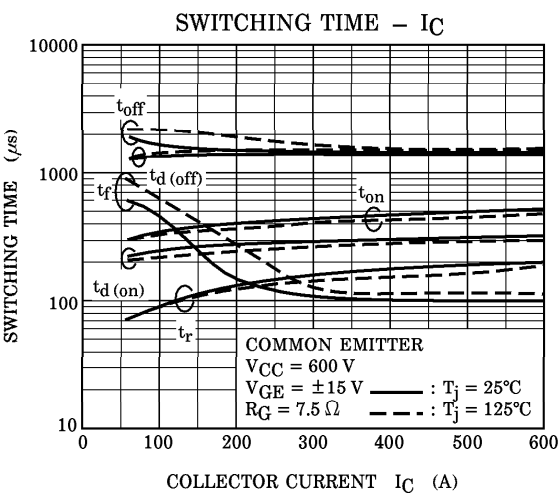
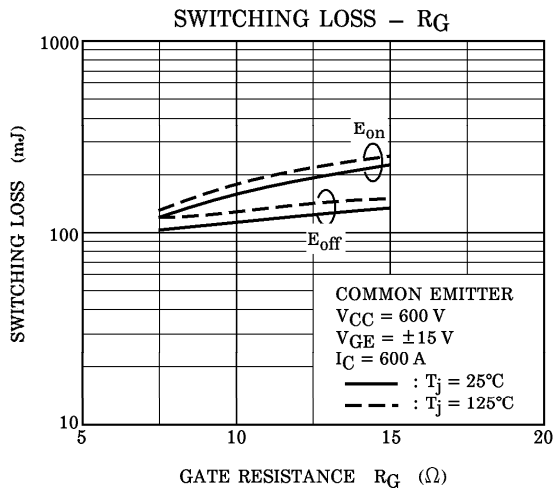
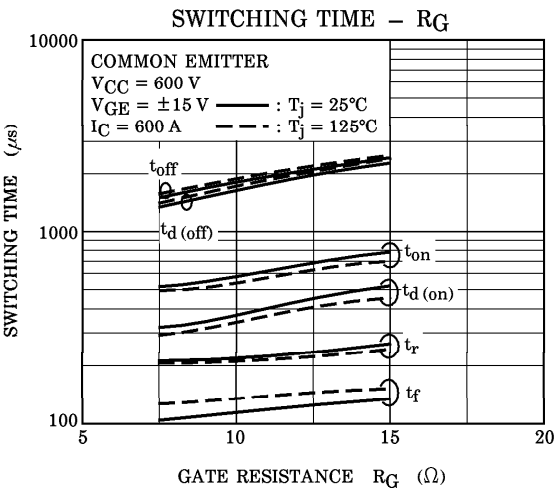
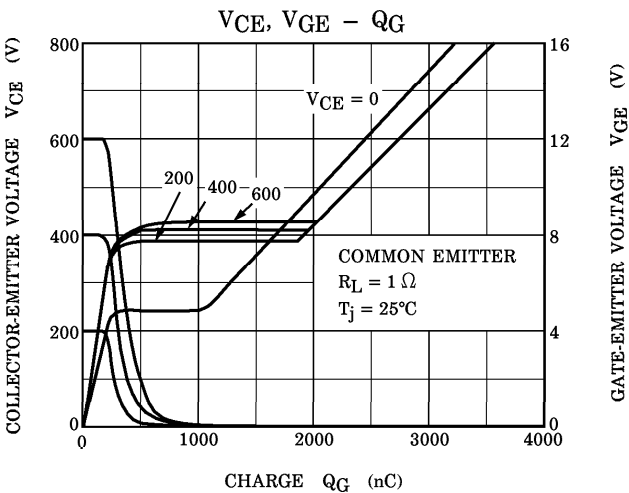
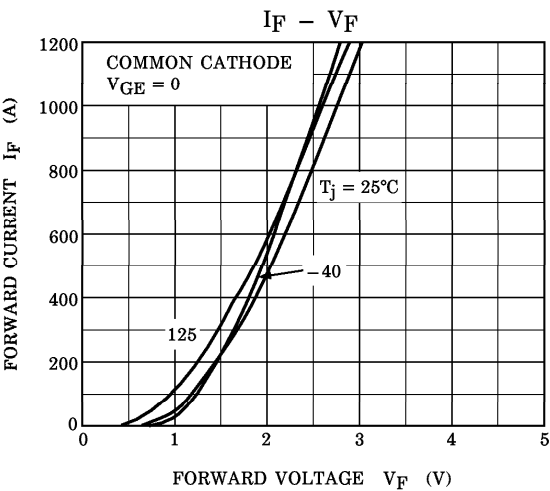
THERMISTOR

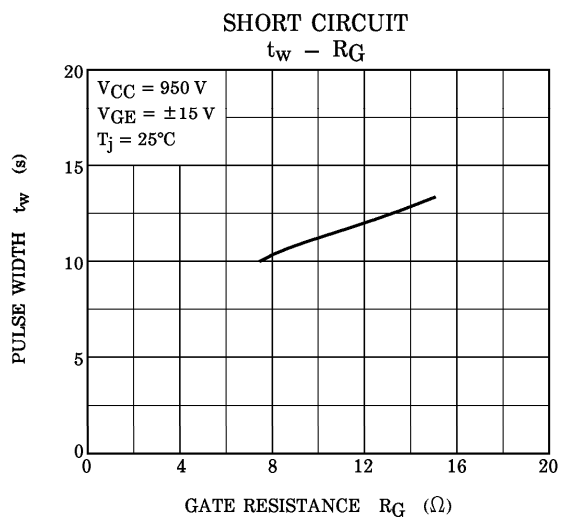
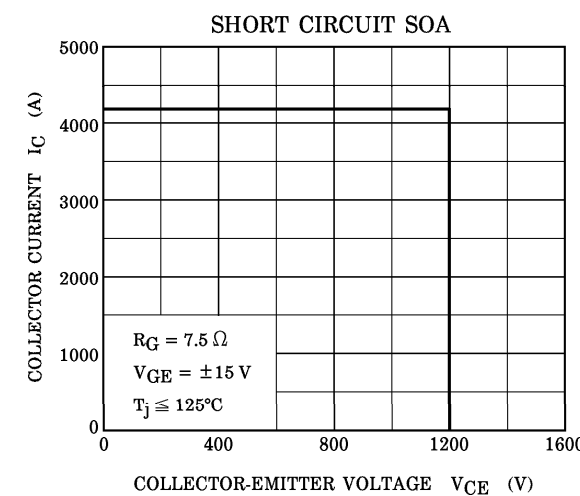
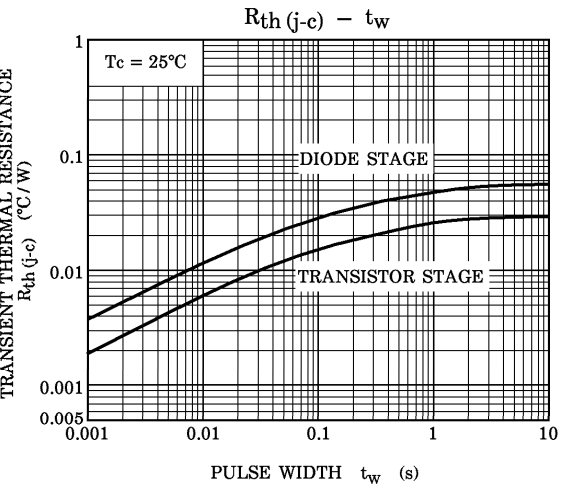
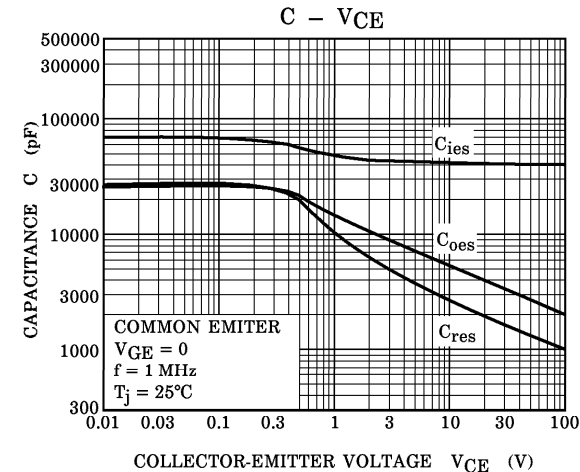
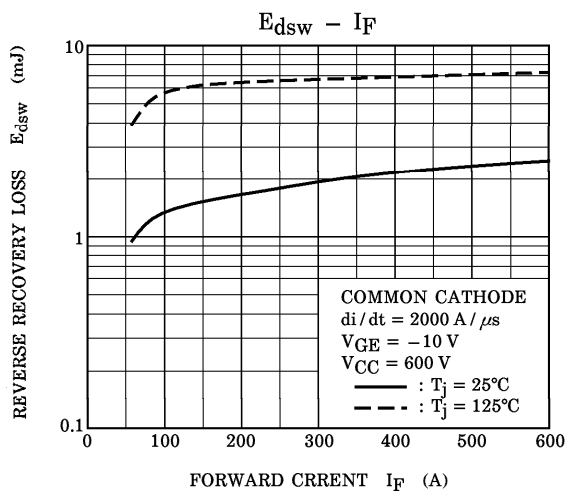
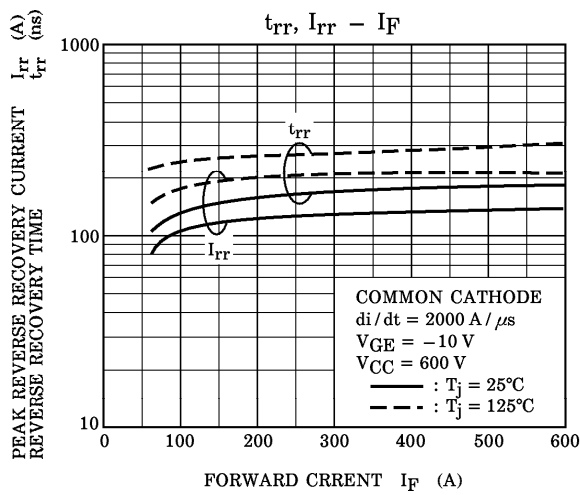
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Zero Power Resistance	R25	Tc = 25°C	—	100	—	kΩ
B Value	B25 / 85	Tc = 25°C / Tc = 85°C	—	4390	—	K
Isolation Voltage		Tc = 25°C	2500	—	—	Vrms

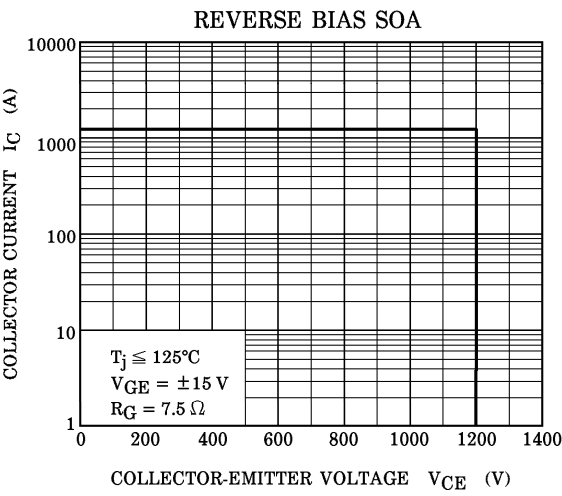
(Note) : Switching time measurement circuit and input/output waveforms











<V_{CE} (sat) RANK>
V_{CE} (sat)

RANK SYMBOL	MIN.	MAX.
21	1.8	2.1
22	1.9	2.2
23	2.0	2.3
24	2.1	2.4
25	2.2	2.5
26	2.3	2.6
27	2.4	2.7
28	2.5	2.8
29	2.6	2.9
30	2.7	3.0
31	2.8	3.1
32	2.9	3.2
33	3.0	3.3

<V_F RANK>
V_F

RANK SYMBOL	MIN.	MAX.
B	1.5	1.8
C	1.7	2.0
D	1.9	2.2
E	2.1	2.4
F	2.3	2.6
G	2.5	2.8
H	2.7	3.0
I	2.9	3.2
J	3.1	3.4
K	3.3	3.6

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